

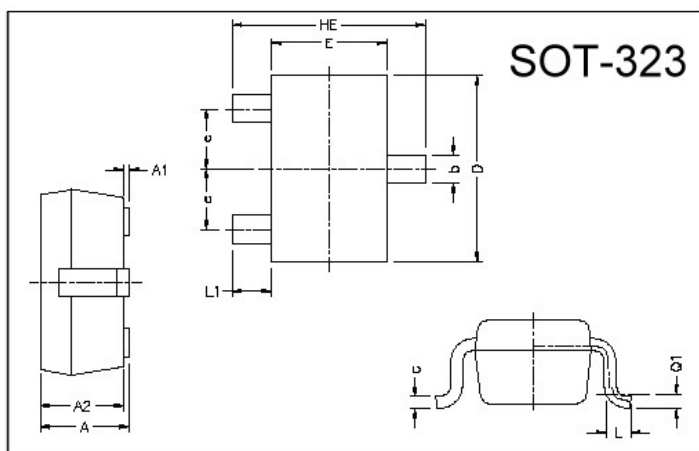
FEATURES

- Ideally suited for automatic insertion
- Epitaxial planar die construction
- Complementary to BC817W

MARKING

16W:5A; 25W:5B; 40W:5C

PACKAGE DIMENSIONS



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.80	1.10	L1	0.42 REF.	
A1	0	0.10	L	0.15	0.35
A2	0.80	1.00	b	0.25	0.40
D	1.80	2.20	c	0.10	0.25
E	1.15	1.35	e	0.65 REF.	
HE	1.80	2.40	Q1	0.15 BSC.	

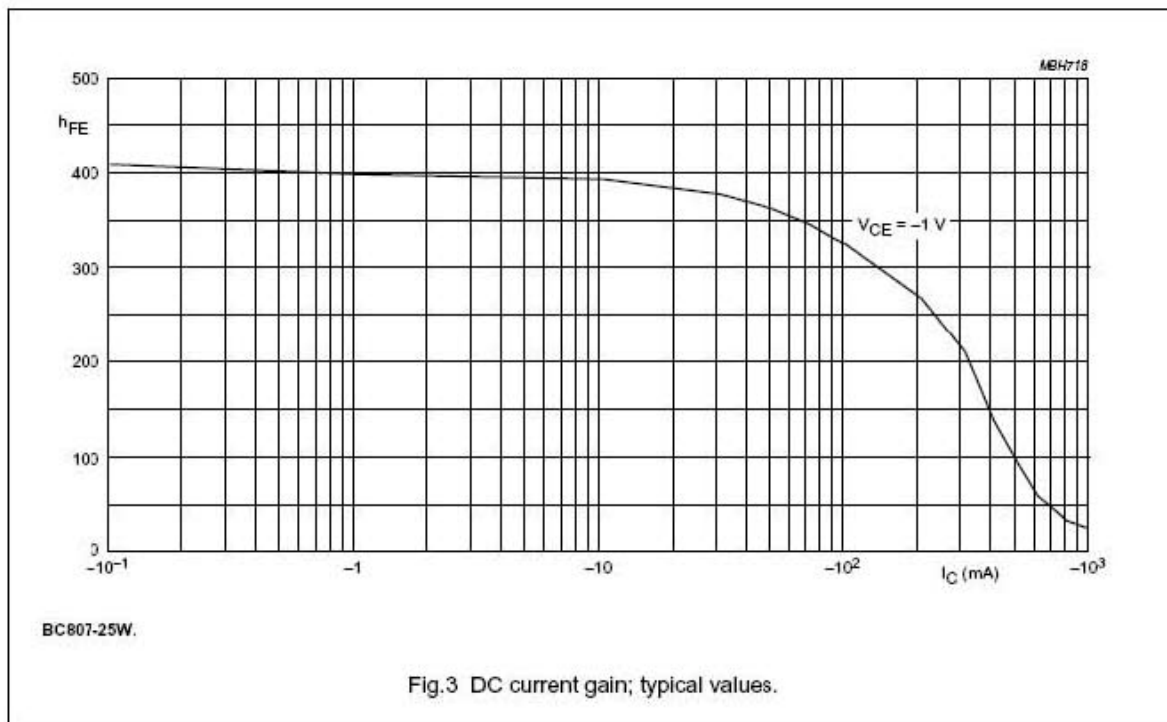
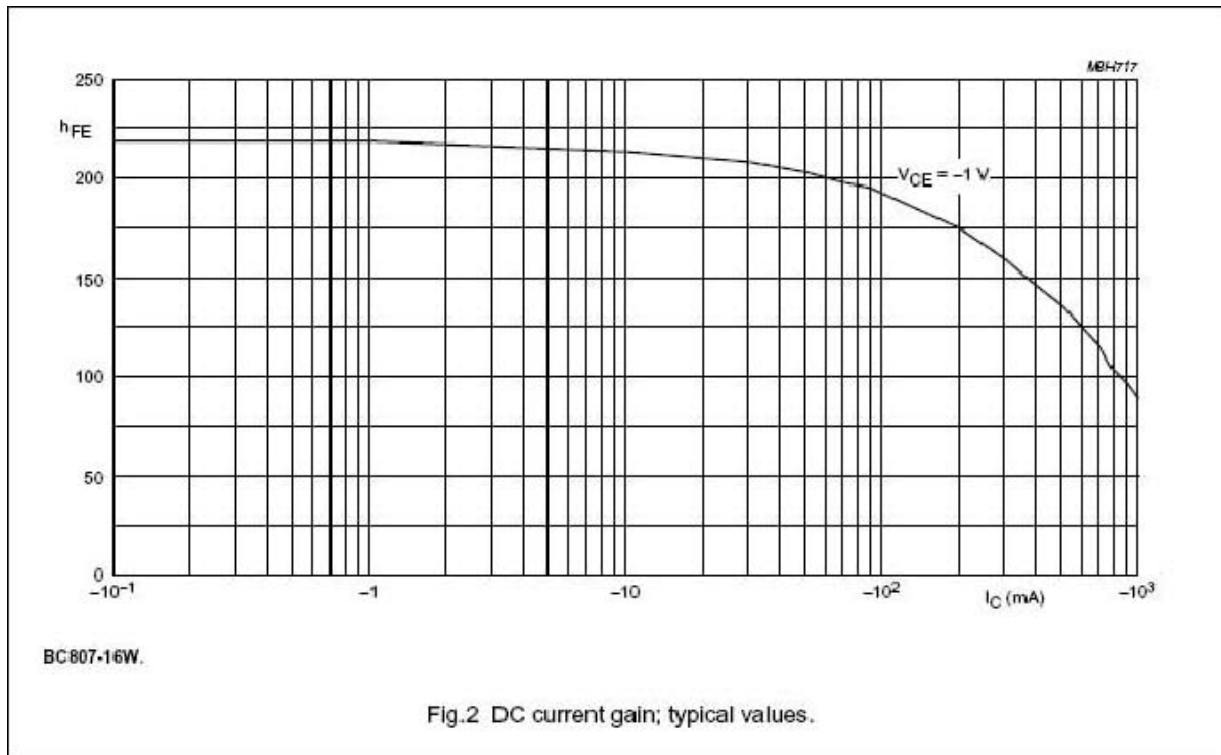
ABSOLUTE MAXIMUM RATINGS at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	-50	V
Collector to Emitter Voltage	V_{CEO}	-45	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	500	mA
Collector Power Dissipation	P_C	200	mW
Junction, Storage Temperature	T_J, T_{STG}	+150, -55 ~ +150	°C

CHARACTERISTICS at Ta = 25°C

Symbol	Min.	Max.	Unit	Test Conditions
BV_{CBO}	-50	-	V	$I_C = -10 \mu A, I_E = 0$
BV_{CEO}	-45	-	V	$I_C = -10 \text{ mA}, I_B = 0$
BV_{EBO}	-5	-	V	$I_E = -1 \mu A, I_C = 0$
I_{CBO}	-	-0.1	μA	$V_{CB} = -20V, I_E = 0$
I_{CEO}	-	-0.2	μA	$V_{CE} = -20V, I_B = 0$
I_{EBO}	-	-0.1	μA	$V_{EB} = -5V, I_C = 0$
$V_{CE(sat)}$	-	-0.7	V	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$
$V_{BE(on)}$	-	-1.2	V	$V_{CE} = -1 \text{ V}, I_C = -500 \text{ mA}$
$h_{FE(1)}$	807-16W	100	250	$V_{CE} = -1 \text{ V}, I_C = -100 \text{ mA}$
	807-25W	160	400	
	807-40W	250	600	
$h_{FE(2)}$	40	-		$V_{CE} = -1 \text{ V}, I_C = -500 \text{ mA}$
f_T	80	-	MHz	$V_{CE} = -5 \text{ V}, I_C = -10 \text{ mA}, f = 100 \text{ MHz}$
C_{OB}	-	10	pF	$V_{CB} = -10V, f=1 \text{ MHz}$

CHARACTERISTIC CURVES



CHARACTERISTIC CURVES

